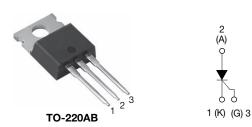


VS-16TTS...PbF Series, VS-16TTS...-M3 Series

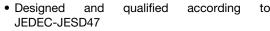
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Thyristor High Voltage, Phase Control SCR, 16 A



PRODUCT SUMMARY				
Package	TO-220AB			
Diode variation	Single SCR			
I _{T(AV)}	10 A			
V_{DRM}/V_{RRM}	800 V, 1200 V			
V_{TM}	1.4 V			
I _{GT}	60 mA			
T_J	- 40 °C to 125 °C			

FEATURES





• 125 °C max. operating junction temperature

Material categorization:
 For definitions of compliance please see www.vishay.com/doc?99912



APPLICATIONS

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge

DESCRIPTION

The VS-16TTS... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operating up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS					
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS					
Capacitive input filter T _A = 55 °C, T _J = 125 °C, common heatsink of 1 °C/W	13.5	17	А		

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
I _{T(AV)}	Sinusoidal waveform	10	۸			
I _{RMS}		16	Α			
V _{DRM} /V _{RRM}	Range (1)	800/1200	V			
I _{TSM}		200	A			
V _T	10 A, T _J = 25 °C	1.4	V			
dV/dt		500	V/µs			
dl/dt		150	A/μs			
T _J	Range	- 40 to 125	°C			

Note

⁽¹⁾ For higher voltage up to 1600 V contact factory

VOLTAGE RATINGS							
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA				
VS-16TTS08PbF, VS-16TTS08-M3	800	800	10				
VS-16TTS12PbF, VS-16TTS12-M3	1200	1200	10				



VS-16TTS...PbF Series, VS-16TTS...-M3 Series

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ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL		TEST CONDITIONS	VALUES		UNITS		
PARAMETER	STIVIBOL	STMBOL TEST CONDITIONS		TYP. MAX.		UNITS		
Maximum average on-state current	$I_{T(AV)}$	T _C = 98 °C, 1	80° conduction, half sine wave	1	0			
Maximum RMS on-state current	I _{RMS}			1	6	Α		
Maximum peak, one-cycle,	L	10 ms sine p	ulse, rated V _{RRM} applied	1	70	Α .		
non-repetitive surge current	I _{TSM}	10 ms sine p	ulse, no voltage reapplied	20	00			
Maximum I ² t for fusing	I ² t	10 ms sine p	ulse, rated V _{RRM} applied	144		A ² s		
iviaximum i-t for fusing	1-1	10 ms sine pulse, no voltage reapplied		200		A-2		
Maximum I ² √t for fusing	I ² √t	t = 0.1 to 10 ms, no voltage reapplied		20	00	A²√s		
Maximum on-state voltage drop	V_{TM}	10 A, T _J = 25 °C		1.4		٧		
On-state slope resistance	r _t	T _L = 125 °C		1.0	mΩ			
Threshold voltage	V _{T(TO)}	11 = 123 0		1	.1	V		
Maximum reverse and direct leakage current	1 /1	T _J = 25 °C	V - Botod V A	0	.5			
waximum reverse and direct leakage current	I _{RM} /I _{DM}	T _J = 125 °C	$V_R = Rated V_{RRM}/V_{DRM}$	1	0			
Holding current	l _Η	Anode supply = 6 V, resistive load, initial I_T = 1 A 16TTS08PbF, 16TTS12PbF, T_J = 25 °C		ı	150	mA		
Maximum latching current	Ι _L	Anode supply = 6 V, resistive load, T _J = 25 °C		Anode supply = 6 V, resistive load, $T_J = 25 ^{\circ}\text{C}$		20	00	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max., linear to } 80 \text{ °C, } V_{DRM} = R_g \text{ - } k = Open$		T _J = T _J max., linear to 80 °C, V _{DRM} = R _g - k = Open		50	00	V/µs
Maximum rate of rise of turned-on current	dI/dt	15		50	A/μs			

TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum peak gate power	P_{GM}		8.0	W		
Maximum average gate power	P _{G(AV)}		2.0	VV		
Maximum peak positive gate current	+ I _{GM}		1.5	Α		
Maximum peak negative gate voltage	- V _{GM}		10	V		
	I _{GT}	Anode supply = 6 V, resistive load, T _J = - 65 °C	90	mA		
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T _J = 25 °C	60			
		Anode supply = 6 V, resistive load, T _J = 125 °C	35			
		Anode supply = 6 V, resistive load, T _J = - 65 °C	3.0			
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	2.0	V		
voltage to trigger		Anode supply = 6 V, resistive load, T _J = 125 °C	1.0	V		
Maximum DC gate voltage not to trigger	V_{GD}	T = 105 °C V = Peted value	0.25			
Maximum DC gate current not to trigger	I_{GD}	T _J = 125 °C, V _{DRM} = Rated value	2.0	mA		

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9			
Typical reverse recovery time	t _{rr}	T _{.I} = 125 °C	4	μs		
Typical turn-off time	tq	1J = 125 G	110			

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THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction and storage temperature range		T _J , T _{Stg}		- 40 to 125	°C	
Maximum thermal resistance, junction to case		R_{thJC}	DC operation	1.3		
Maximum thermal resistance, junction to ambient		R_{thJA}		62	°C/W	
Typical thermal resistance, case to heatsink		R_{thCS}	Mounting surface, smooth and greased	0.5		
Approximate weight				2	g	
Approximate weight				0.07	OZ.	
Mounting torque	minimum			6 (5)	kgf · cm	
wounting torque	maximum			12 (10)	(lbf · in)	
Madding daying			Coop at the TO 000 A D	16T7	TS08	
Marking device		Case style TO-220AB		16TTS12		

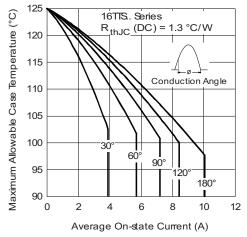


Fig. 1 - Current Rating Characteristics

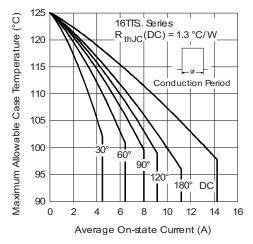


Fig. 2 - Current Rating Characteristics

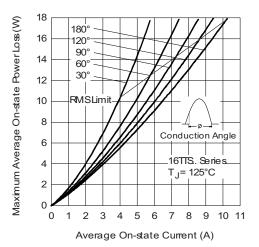


Fig. 3 - On-State Power Loss Characteristics

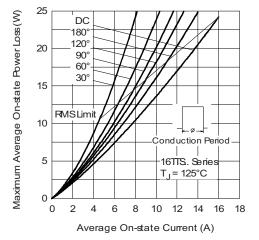


Fig. 4 - On-State Power Loss Characteristics

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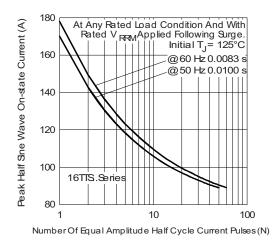


Fig. 5 - Maximum Non-Repetitive Surge Current

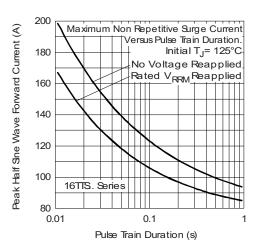


Fig. 6 - Maximum Non-Repetitive Surge Current

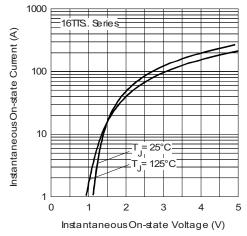


Fig. 7 - On-State Voltage Drop Characteristics

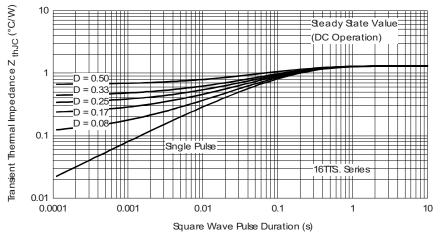


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

VS-16TTS...PbF Series, VS-16TTS...-M3 Series

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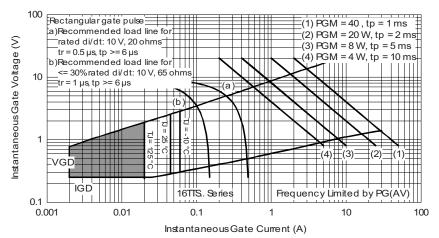
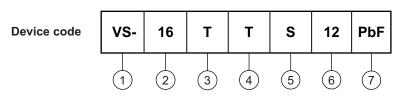


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE



1 - Vishay Semiconductors product

2 - Current rating

3 - Circuit configuration:

T = Single thyristor

4 - Package:

T = TO-220AB

5 - Type of silicon:

S = Converter grade

6 - Voltage code x 100 = V_{RRM} - 08 = 800 V 12 = 1200 V

7 - Environmental digit:

PbF = Lead (Pb)-free and RoHS compliant

-M3 = Halogen-free, RoHS compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-16TTS08PbF	50	1000	Antistatic plastic tubes			
VS-16TTS08-M3	50	1000	Antistatic plastic tubes			
VS-16TTS12PbF	50	1000	Antistatic plastic tubes			
VS-16TTS12-M3	50	1000	Antistatic plastic tubes			

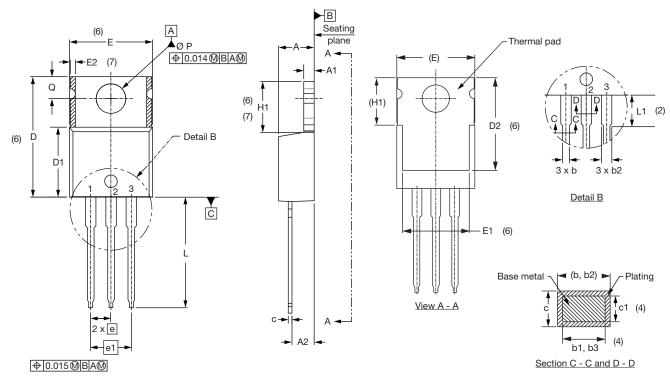
LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?95222</u>				
Dort marking information	TO-220AB PbF	www.vishay.com/doc?95225		
Part marking information	TO-220AB -M3	www.vishay.com/doc?95028		



Vishay Semiconductors

TO-220AB

DIMENSIONS in millimeters and inches



Lead tip

Lead assignments

<u>Diodes</u>

- 1. Anode/open
- 2. Cathode
- 3. Anode

Conforms to JEDEC outline TO-220AB

SYMBOL	MILLIN	IILLIMETERS INCHES IIN. MAX. MIN. MAX.		NOTES	
STMBOL	MIN.			MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

SYMBOL	MILLIMETERS		INCHES		NOTES	
STIMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Е	10.11	10.51	0.398	0.414	3, 6	
E1	6.86	8.89	0.270	0.350	6	
E2	-	0.76	-	0.030	7	
е	2.41	2.67	0.095	0.105		
e1	4.88	5.28	0.192	0.208		
H1	6.09	6.48	0.240	0.255	6, 7	
L	13.52	14.02	0.532	0.552		
L1	3.32	3.82	0.131	0.150	2	
ØΡ	3.54	3.73	0.139	0.147		
Q	2.60	3.00	0.102	0.118		
θ	90° to 93°		90° t	o 93°		

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline



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Vishay

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AMEYA360 Components Supply Platform

Authorized Distribution Brand:

























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